

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph starting on page 4, line 23 as follows:

FIG. 5 is an illustration of a stacked microelectronic device, as known in the art.

Please amend the paragraph starting on page 17, line 18 as follows:

FIG. 4 illustrates a process flow diagram 159, illustrating the processes used to form a stacked device with an underfill in accordance with at least one embodiment. The flowchart 159 illustrated in FIG. 4 may be used to substantially perform the phases of formation of a stacked device as illustrated in **FIG. 1** **FIG. 2**, for example, although the order presented does not infer a particular order nor limit the process flow to just these discrete functions. In this embodiment, one or more substrates with exposed structures are formed at functional block 160; a photodefineable material or combination of photodefineable and/or non-photodefineable materials are deposited at functional block 162 to form a material layer; the material layer is exposed at functional block 164; the material layer may be cured at functional block 166; the exposed photodefineable material of the material layer may be etched at functional block 168; the substrate may be aligned with one or more other substrates at functional block 170; and at functional block 172, the one or more substrates are bonded to the substrates to which they are aligned.